

isc Silicon NPN RF Transistor

2SC4703

DESCRIPTION

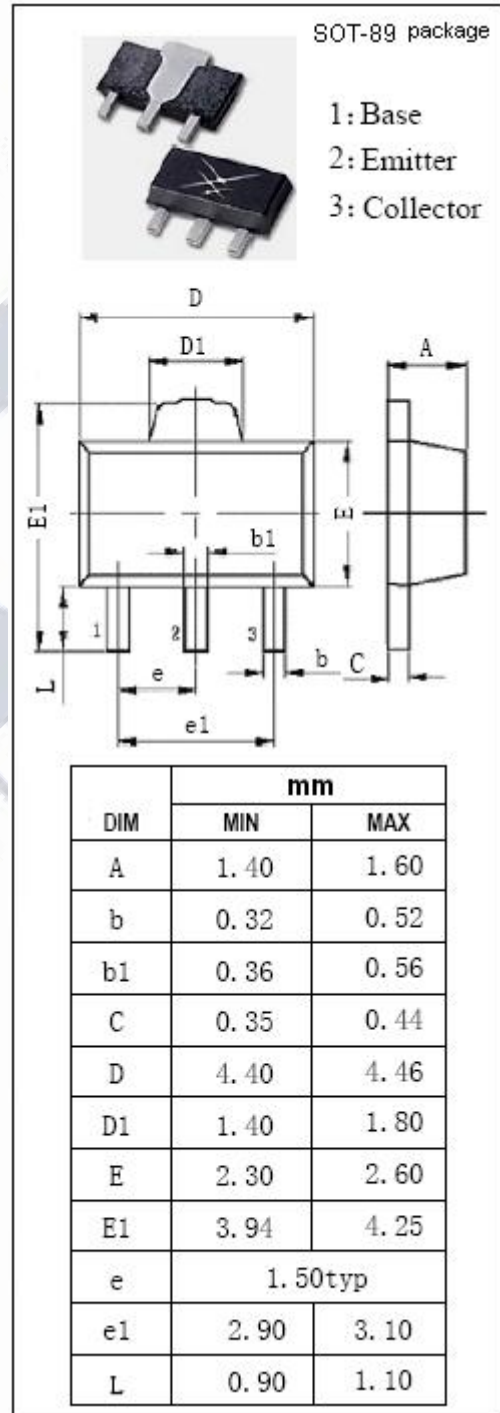
- Low Distortion at Low Supply Voltage.
IM₂- 55 dB TYP., IM₃- 76 dB TYP.
@V_{CE} = 5 V, I_c = 50 mA, V_O = 105dB μ /75 Ω
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for low distortion ,low noise RF amplifier operating with low supply voltage (V_{CE} = 5V).

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	25	V
V _{CEO}	Collector-Emitter Voltage	12	V
V _{EBO}	Emitter-Base Voltage	2.5	V
I _c	Collector Current-Continuous	0.15	A
P _c	Collector Power Dissipation @T _c =25°C	1.8	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



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ELECTRICAL CHARACTERISTICS

 $T_c=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
I_{CBO}	Collector Cutoff Current	$V_{CB}=20\text{V}; I_E=0$			1.5	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=2\text{V}; I_C=0$			1.5	μA
h_{FE}	DC Current Gain	$I_C=5\text{mA}; V_{CE}=5\text{V}$	50		250	
f_T	Current-Gain—Bandwidth Product	$I_C=5\text{mA}; V_{CE}=5\text{V}$		6.0		GHz
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=5\text{V}; f=1.0\text{MHz}$		1.5	2.5	pF
$ S_{21e} ^2$	Insertion Power Gain	$I_C=50\text{mA}; V_{CE}=5\text{V}; f=1.0\text{GHz}$	6.5	8.3		dB
$ S_{21e} ^2$	Insertion Power Gain	$I_C=20\text{mA}; V_{CE}=10\text{V}; f=1.0\text{GHz}$		8.5		dB
NF	Noise Figure	$I_C=50\text{mA}; V_{CE}=5\text{V}; f=1.0\text{GHz}$		2.3	3.5	dB
IM_2	2nd Intermodulation Distortion	$V_{CE}=5\text{V}, I_C=50\text{mA},$ $V_O=105\text{ dB } \mu\text{V}/75\ \Omega,$ $f=190\text{ MHz} - 90\text{ MHz}$		-55		dB
		$V_{CE}=10\text{V}, I_C=50\text{mA},$ $V_O=105\text{ dB } \mu\text{V}/75\ \Omega,$ $f=190\text{ MHz} - 90\text{ MHz}$		-63		
IM_3	3rd Intermodulation Distortion	$V_{CE}=5\text{V}, I_C=50\text{mA},$ $V_O=105\text{ dB } \mu\text{V}/75\ \Omega,$ $f=2 \times 190\text{ MHz} - 200\text{ MHz}$		-76		dB
		$V_{CE}=10\text{V}, I_C=50\text{mA},$ $V_O=105\text{ dB } \mu\text{V}/75\ \Omega,$ $f=2 \times 190\text{ MHz} - 200\text{ MHz}$		-81		

◆ h_{FE} Classification

Class	SH	SF	SE
Marking	SH	SF	SE
h_{FE}	50-100	80-160	125-250